Electronic Supplementary Material (ESI) for CrystEngComm.

Supporting Information

Controllable growth of large-size α-GeTe nanosheets with ferroelectricity by substrate pre-annealing

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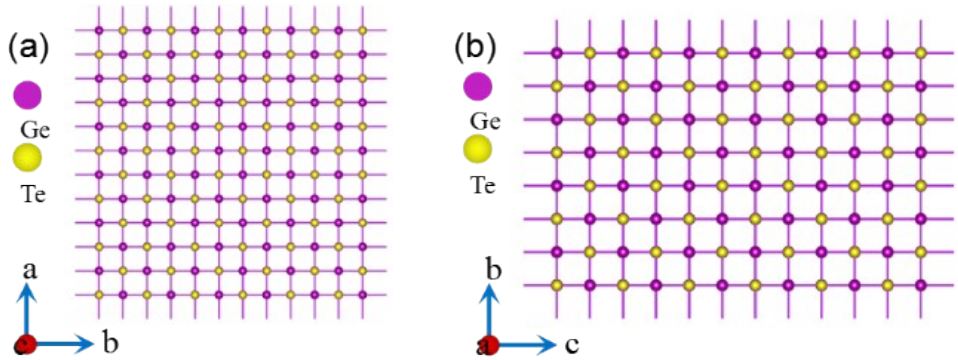

Fig. S1 (a) Top view structure of β-GeTe crystal. (b) Side view structure of β-GeTe crystal.

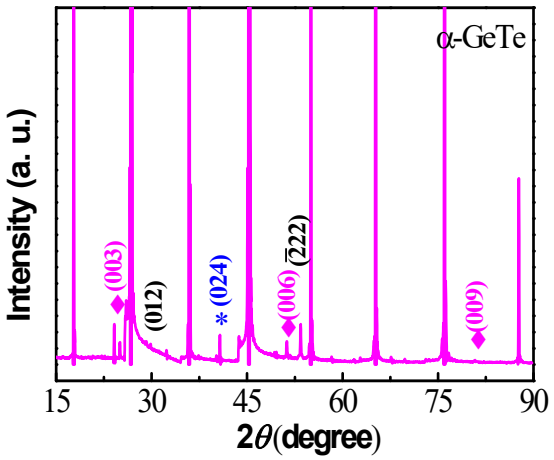

Fig. S2 XRD results of the as-grown α-GeTe nanosheets on annealed mica substrate.

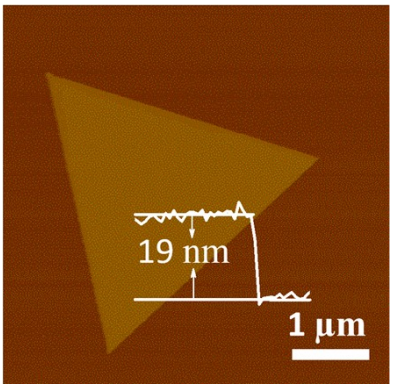

Fig. S3 Corresponding AFM images of to the Raman signal.

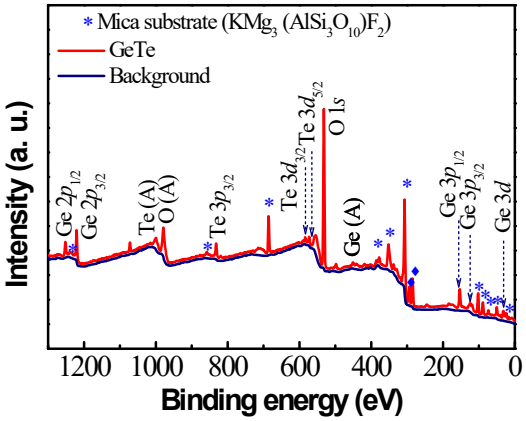

Fig. S4 Wide-scan survey XPS spectra of α-GeTe nanosheets.